



Chemical Characterization Techniques of Qubits

Akshay Murthy

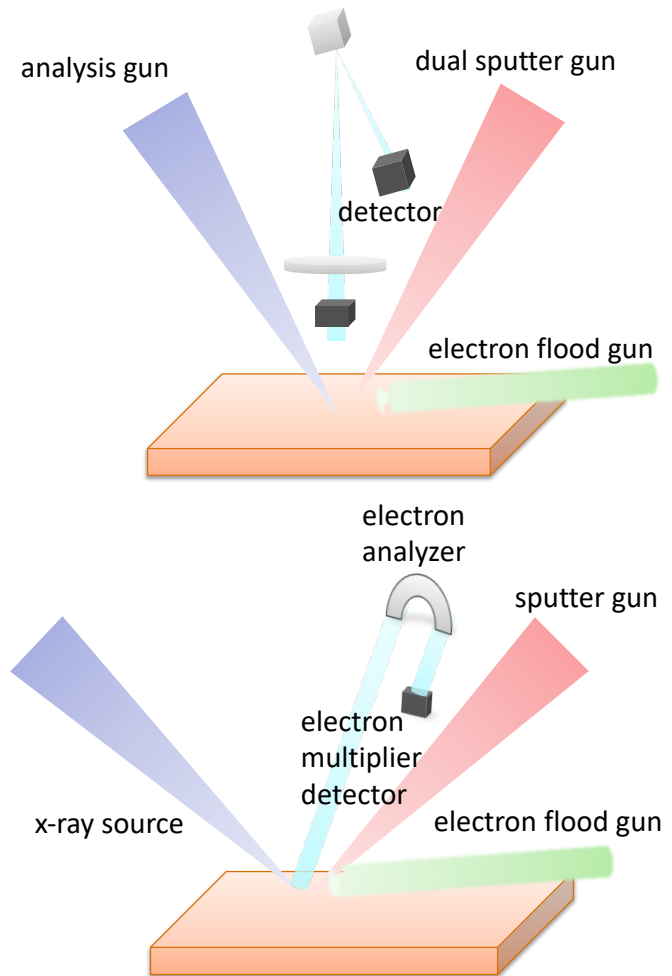
Group Leader, Materials for Quantum Devices

Deputy Head, Qubits and Materials Department, SQMS Division

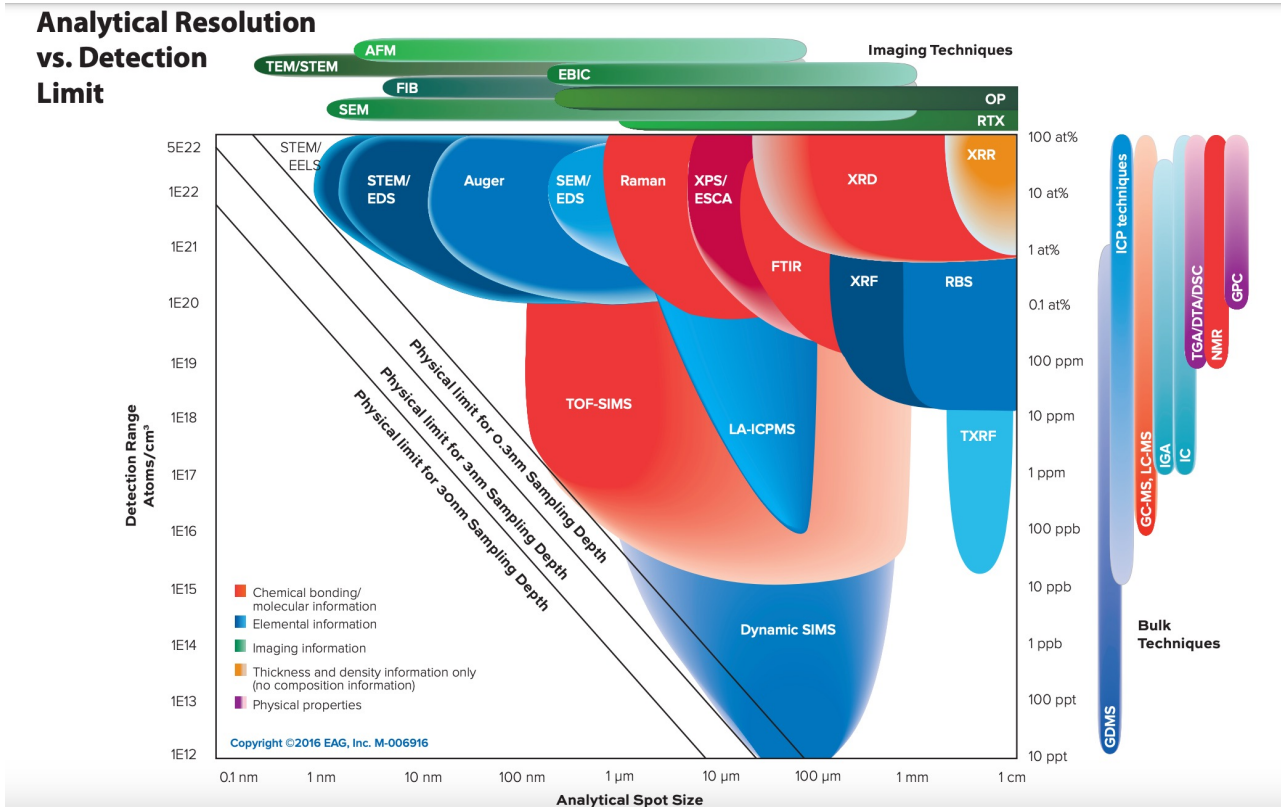
August 14th, 2023

Outline

- Overview of Chemical Characterization Techniques
- Time of Flight Secondary Ion Mass Spectrometry (ToF-SIMS)
- X-ray Photoelectron Spectroscopy (XPS)



Chemical Characterization Techniques



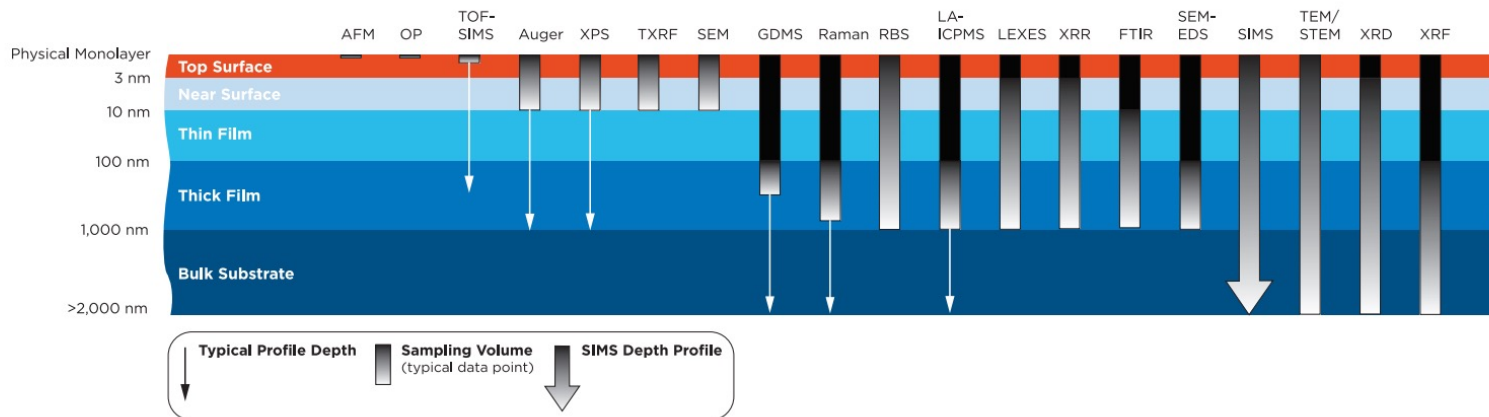
Source: EAG

Chemical Characterization Techniques



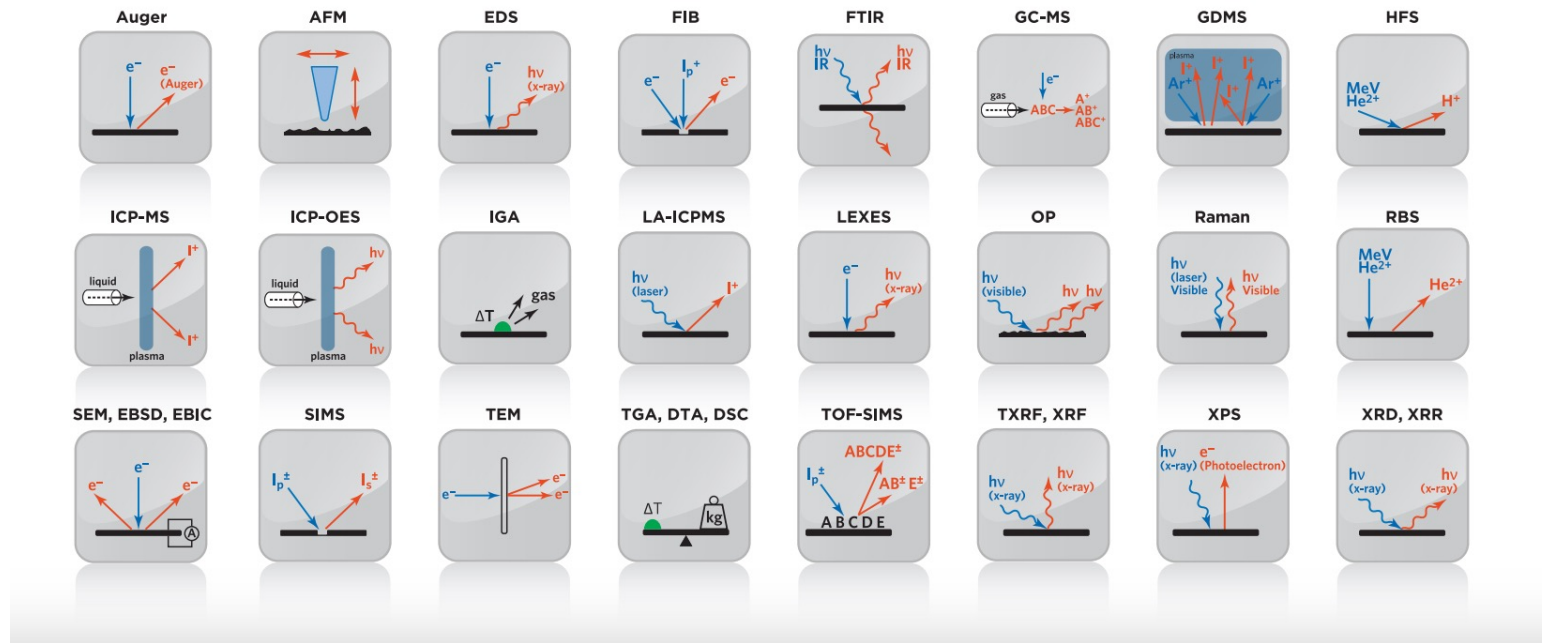
Typical Analysis Depths for Techniques

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EAG.COM



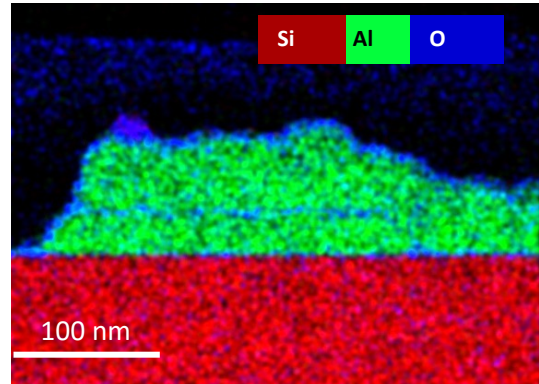
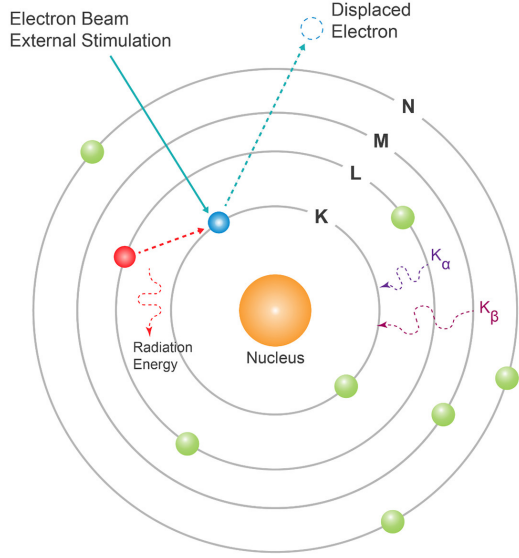
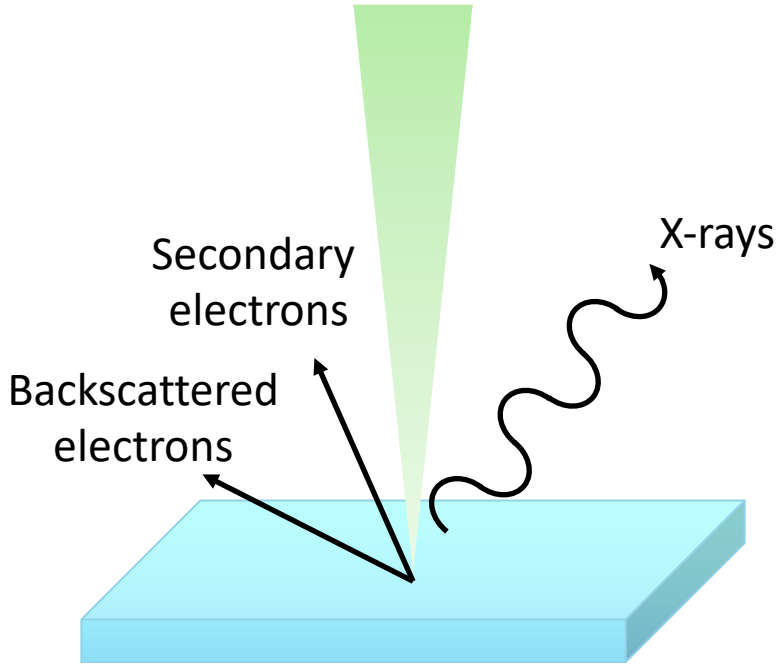
Source: EAG

Chemical Characterization Techniques



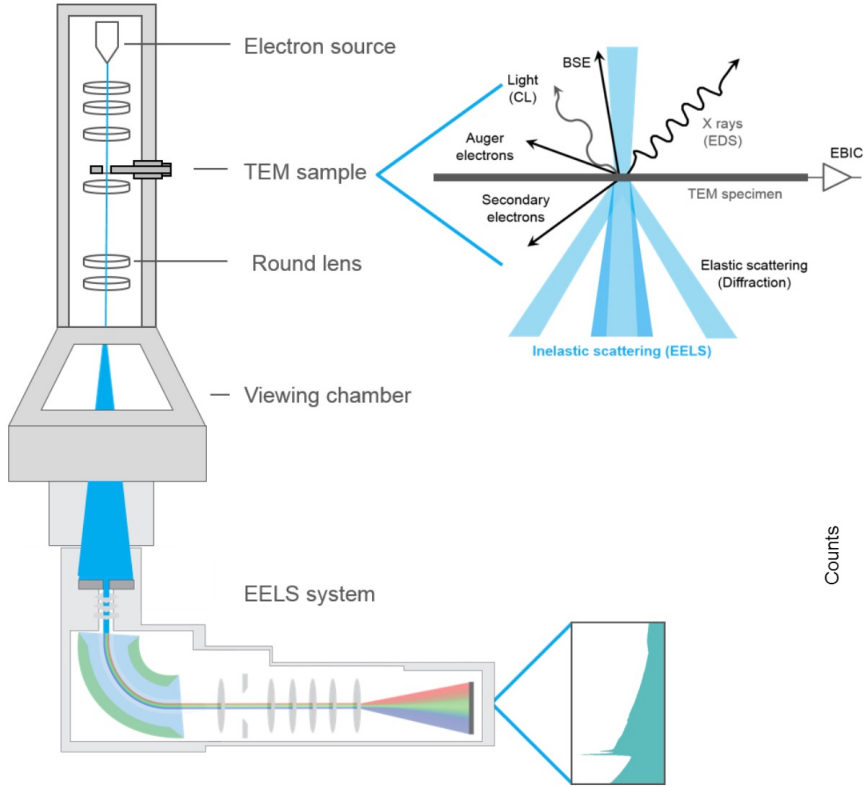
Source: EAG

Chemical Characterization Techniques - EDS

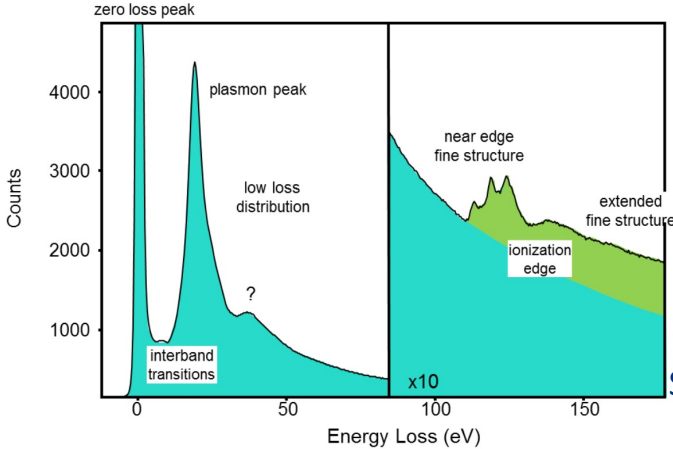


Courtesy of Prof. Lin Zhou

Chemical Characterization Techniques - EELS

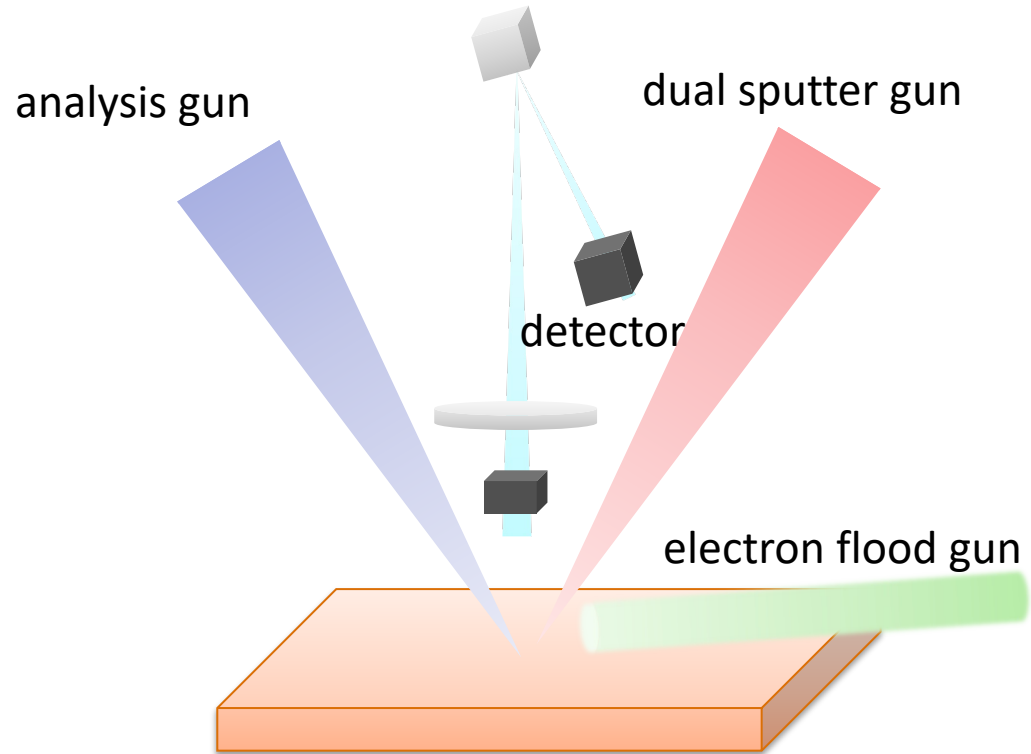
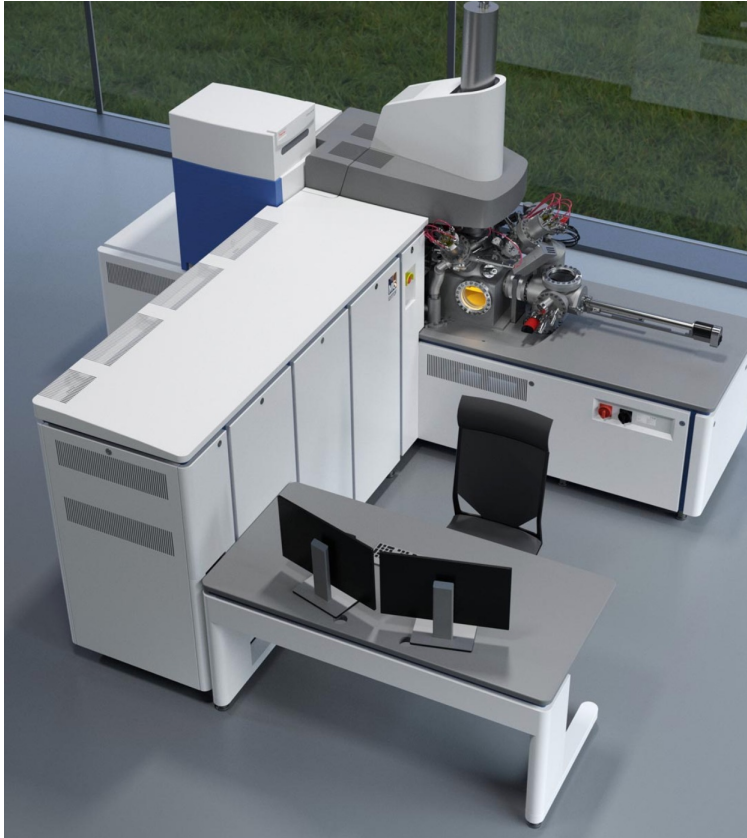


Bonding and oxidation state
(density of unoccupied states)



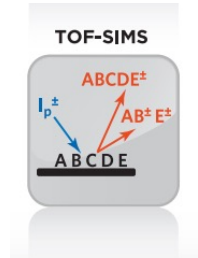
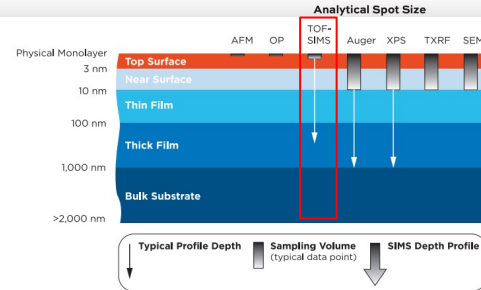
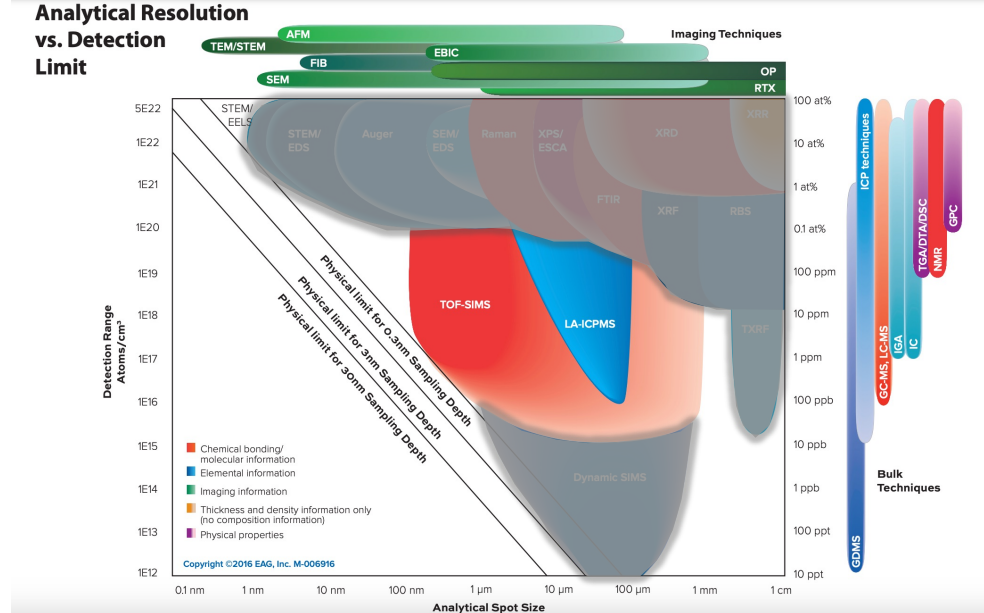
Source: Gatan

ToF-SIMS



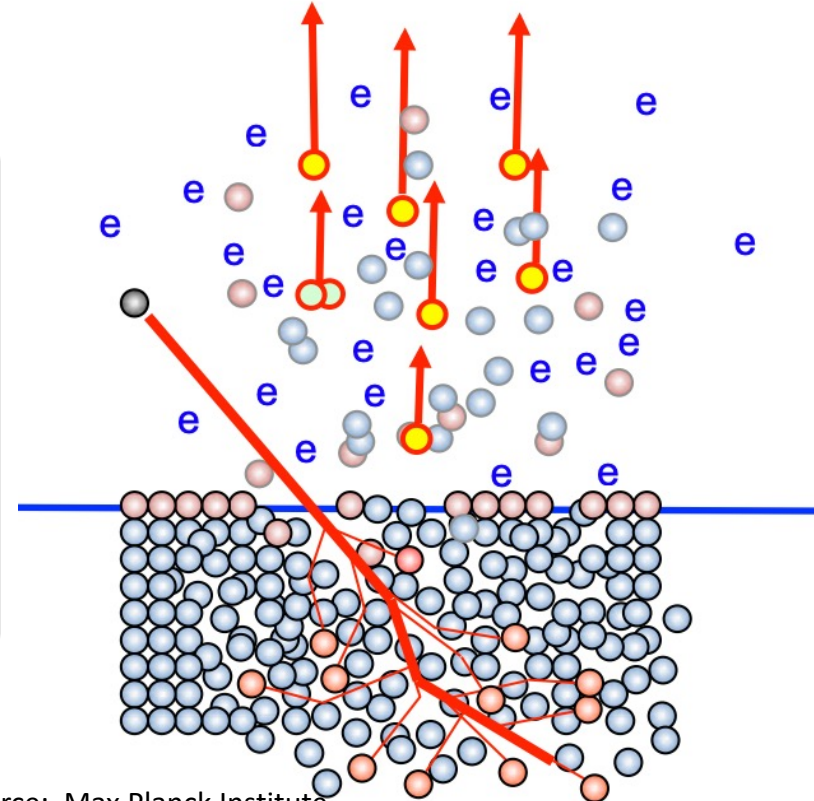
ToF-SIMS: Basics

- Very sensitive surface analytical technique
- Provides elemental & molecular information
- 3D analysis
- Detection of low atomic number elements



ToF-SIMS: Surface Bombardment

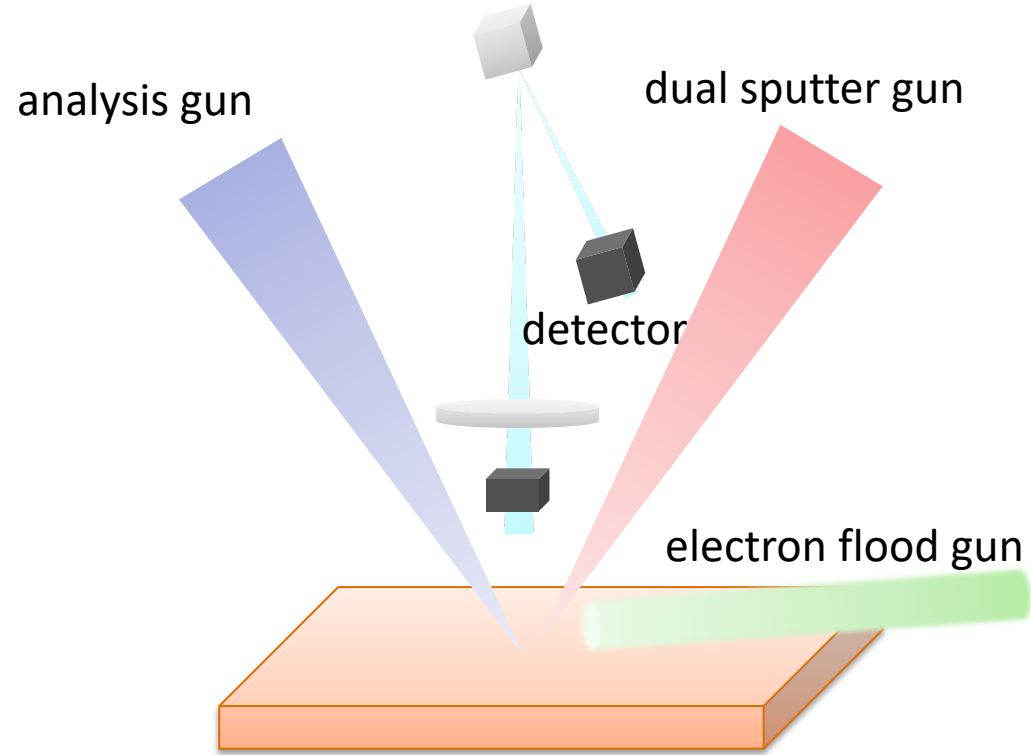
- Surface is bombarded by 30 keV primary ions
- Primary ion energy transferred to surface atoms and molecular compounds through atomic collisions
 - secondary ions overcome surface binding energy



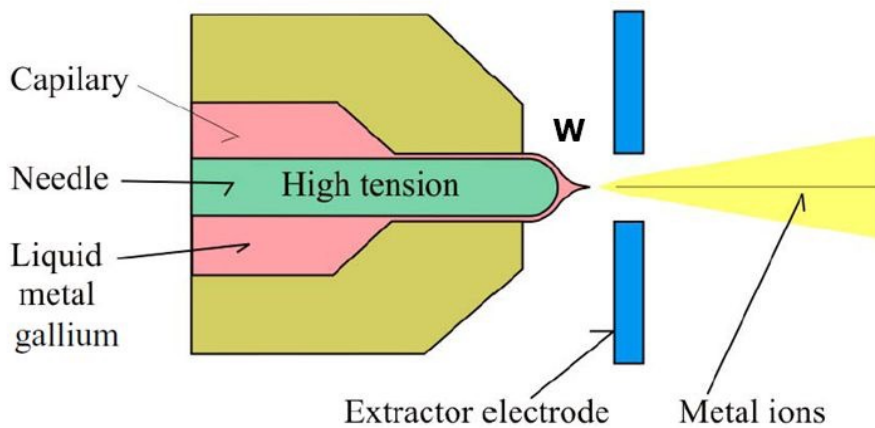
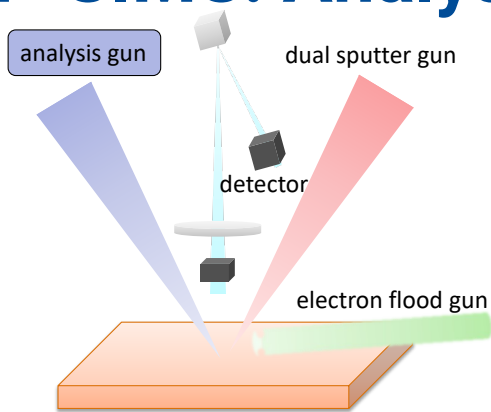
Source: Max Planck Institute

ToF-SIMS

- Analysis gun
- Dual sputter gun
- Electron flood gun
- Detector



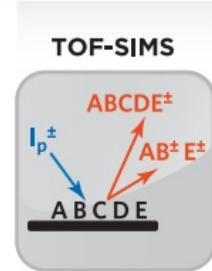
ToF-SIMS: Analysis Gun - Source



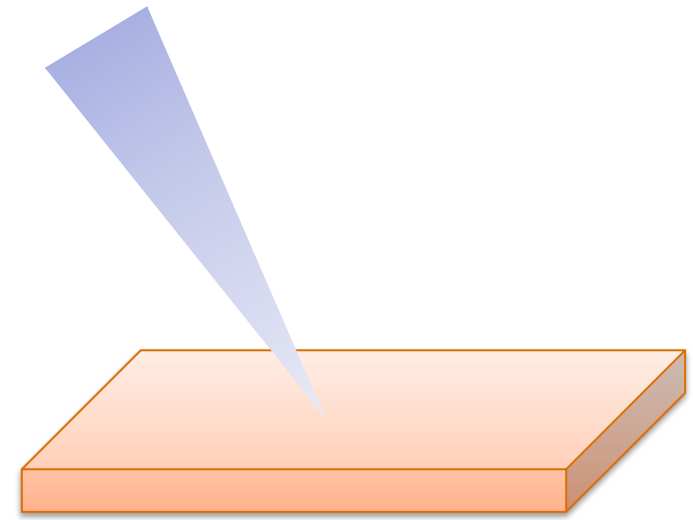
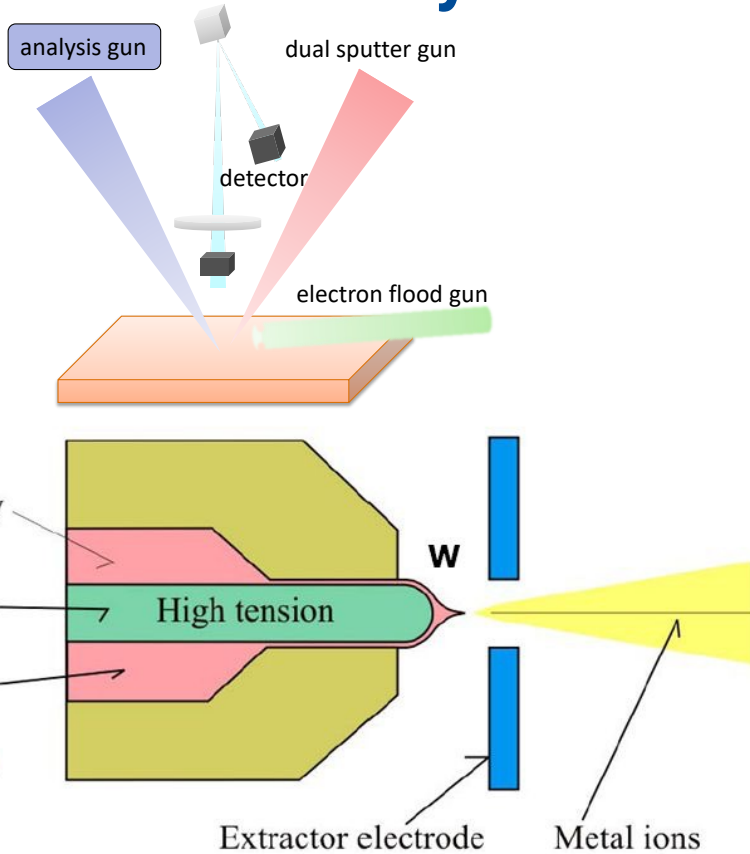
Periodic Table of the Elements

Number	Symbol	Name	Mass
1	H	Hydrogen	1.008
2	He	Helium	4.003
3	Li	Lithium	6.941
4	Be	Beryllium	9.012
5	B	Boron	10.811
6	C	Carbon	12.011
7	N	Nitrogen	14.007
8	O	Oxygen	15.999
9	F	Fluorine	18.998
10	Ne	Neon	20.180
11	Na	Sodium	22.990
12	Mg	Magnesium	24.305
13	Al	Aluminum	26.982
14	Si	Silicon	28.086
15	P	Phosphorus	30.974
16	S	Sulfur	32.06
17	Cl	Chlorine	35.453
18	Ar	Argon	39.948
19	K	Potassium	39.098
20	Ca	Calcium	40.078
21	Sc	Scandium	44.956
22	Ti	Titanium	47.867
23	V	Vanadium	50.942
24	Cr	Chromium	51.996
25	Mn	Manganese	54.938
26	Fe	Iron	55.845
27	Co	Cobalt	58.933
28	Ni	Nickel	58.693
29	Cu	Copper	63.546
30	Zn	Zinc	65.38
31	Ga	Gallium	69.723
32	Ge	Germanium	72.631
33	As	Arsenic	74.922
34	Se	Selenium	78.971
35	Br	Bromine	79.904
36	Kr	Krypton	83.798
37	Rb	Rubidium	85.468
38	Sr	Strontium	87.62
39	Y	Yttrium	88.906
40	Zr	Zirconium	91.224
41	Nb	Niobium	92.906
42	Mo	Molybdenum	95.95
43	Tc	Technetium	98.907
44	Ru	Ruthenium	101.07
45	Rh	Rhodium	102.906
46	Pd	Palladium	106.42
47	Ag	Silver	107.868
48	Cd	Cadmium	112.414
49	In	Indium	114.818
50	Sn	Sn	118.710
51	Sb	Antimony	121.760
52	Te	Tellurium	127.6
53	I	Iodine	126.904
54	Xe	Xenon	131.293
55	Cs	Cesium	132.905
56	Ba	Barium	137.328
57-71	Lanthanide Series		
72	Hf	Hafnium	178.49
73	Ta	Tantalum	180.948
74	W	Tungsten	183.84
75	Re	Rhenium	186.207
76	Os	Osmium	190.23
77	Ir	Iridium	192.22
78	Pt	Platinum	195.085
79	Au	Gold	196.967
80	Hg	Mercury	200.592
81	Tl	Thallium	204.383
82	Pb	Lead	207.2
83	Bi	Bismuth	208.980
84	Po	Polonium	[209]
85	At	Astatine	[209]
86	Rn	Radon	[222]
87	Fr	Francium	[223]
88	Ra	Radium	[226]
89-103	Actinide Series		
104	Rf	Rutherfordium	[261]
105	Db	Dubnium	[262]
106	Sg	Seaborgium	[266]
107	Bh	Berkelium	[267]
108	Hs	Hassium	[277]
109	Mt	Moscovium	[288]
110	Ds	Darmstadtium	[285]
111	Rg	Roentgenium	[282]
112	Cn	Copernicium	[285]
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116	Lv	Livermorium	[293]
117	Ts	Tennessine	[294]
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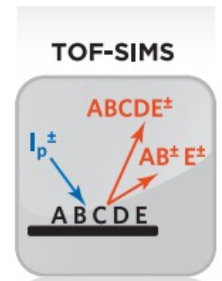
- Beam Energy: ~ 10-30keV
- Probe Size: <1um
- Information Depth: ~ 1-2 nm



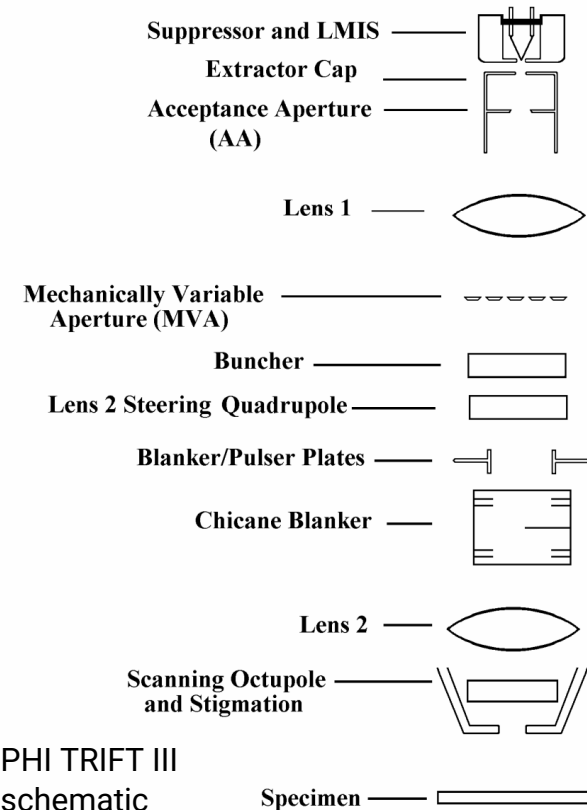
ToF-SIMS: Analysis Gun - Source



- Pulsed ion beam → reduce damage to sample surface
- Pulse length ~ 500 ps



ToF-SIMS: Analysis Gun - Optics



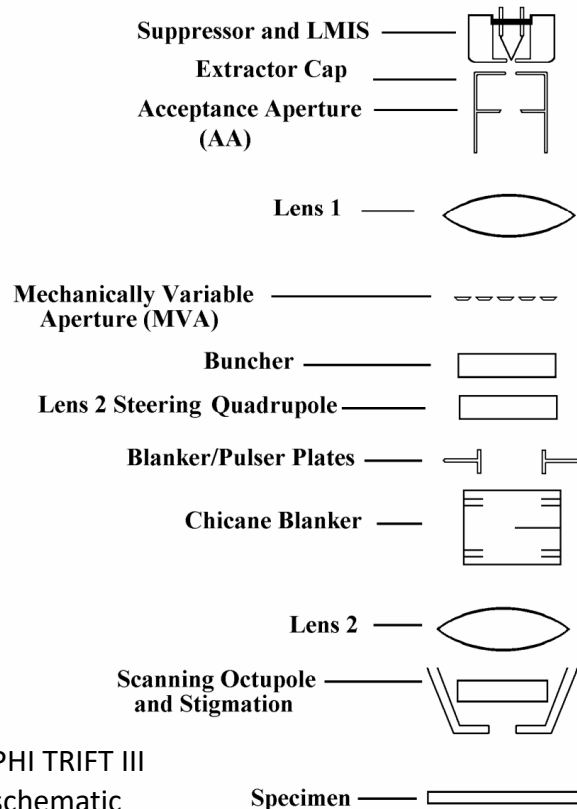
Extractor: Accelerating voltage used to extract ions from source and generate ion beam

Suppressor: Voltage used to improve distribution of extracted ions

Lens 1 (Condenser Lens): Parallelizes ion beam to form an ion probe

Mechanically Variable Aperture: Defines ion current – array of apertures used to set probe size

ToF-SIMS: Analysis Gun - Optics



Blanker/Pulsor Plates: Pulses ion beam to reduce surface damage

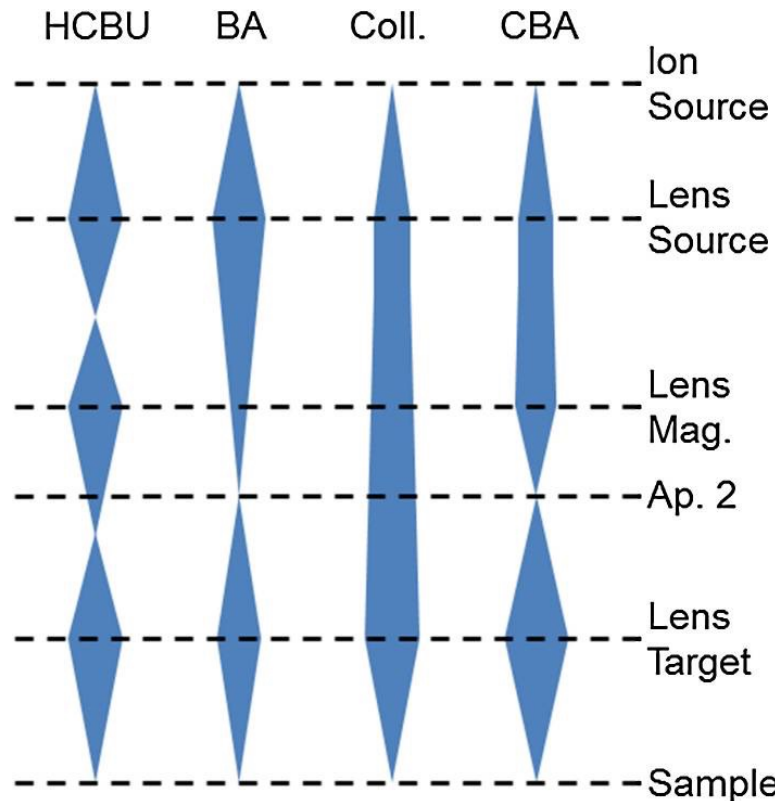
Lens 2 (Objective Lens): Focuses ion beam onto sample

Scanning Octupole: Allows for rastering ion beam across region of interest

Stigmation: Applies weak electric field to reduce astigmatism in ion beam

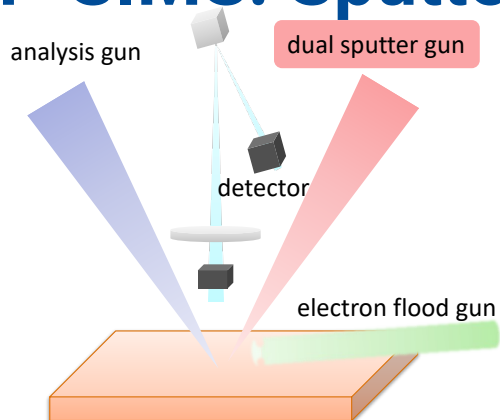
ToF-SIMS: Analysis Gun – Different Modes

Operation mode	HCBU	BA	Collimated	CBA
Lens Source	~3150 V	~3300 V	~3900 V	~3750 V
Lens Mag	~14.8 kV	0 V	0 V	12–13 kV
DC-current	~15 nA	0.4–0.7 nA	50 pA	70–100 pA
Crossovers	2	1	0	1
Lateral resolution	2–10 μm	~250 nm	~100 nm	~100 nm
Mass resolution	~11,000	~200	~200	~200



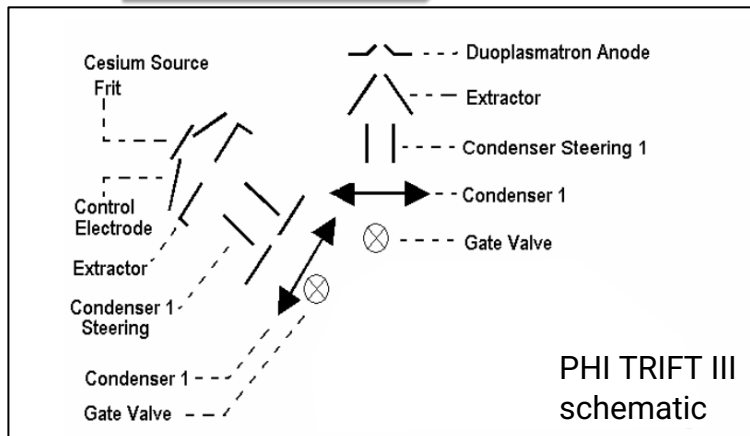
Kubicek M, et al. Appl Surf Sci. 2014 Jan 15;289(100):407-416. doi: 10.1016/j.apsusc.2013.10.177. PMID: 24748701; PMCID: PMC3990430.

ToF-SIMS: Sputter Gun - Source

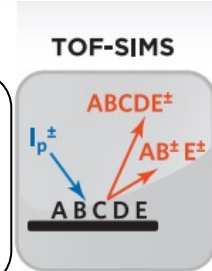


Periodic Table of the Elements

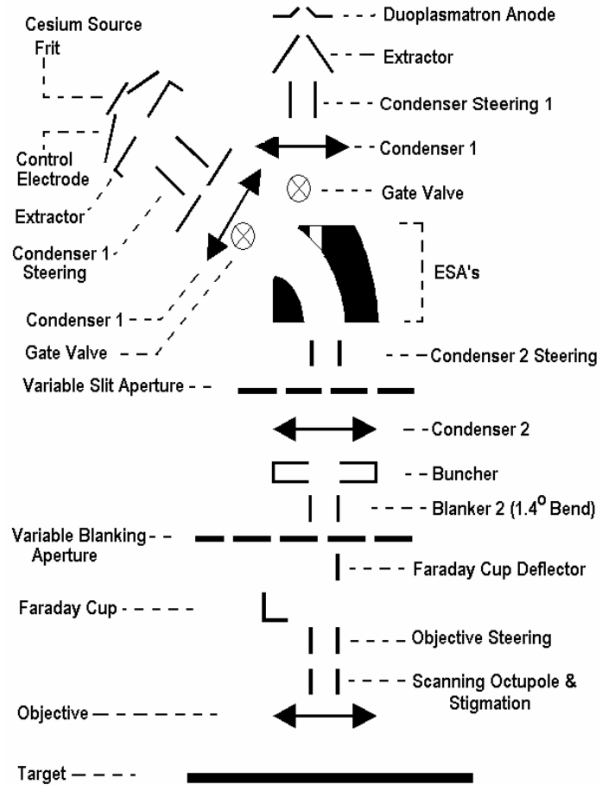
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38	Sr	Strontium	87.62	
39	Y	Yttrium	88.906	
40	Zr	Zirconium	91.224	
41	Nb	Niobium	92.906	
42	Mo	Molybdenum	95.95	
43	Tc	Technetium	98.907	
44	Ru	Ruthenium	101.07	
45	Rh	Rhodium	102.906	
46	Pd	Palladium	106.42	
47	Ag	Silver	107.868	
48	Cd	Cadmium	112.414	
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116	Lv	Livermorium	[293]	
117	Ts	Tennessine	[294]	
118	Og	Oganesson	[294]	



- Beam Energy: ~ 0.5-2 keV
- Probe Size: >1 μm
- Depth Resolution: ~ 2-5 nm



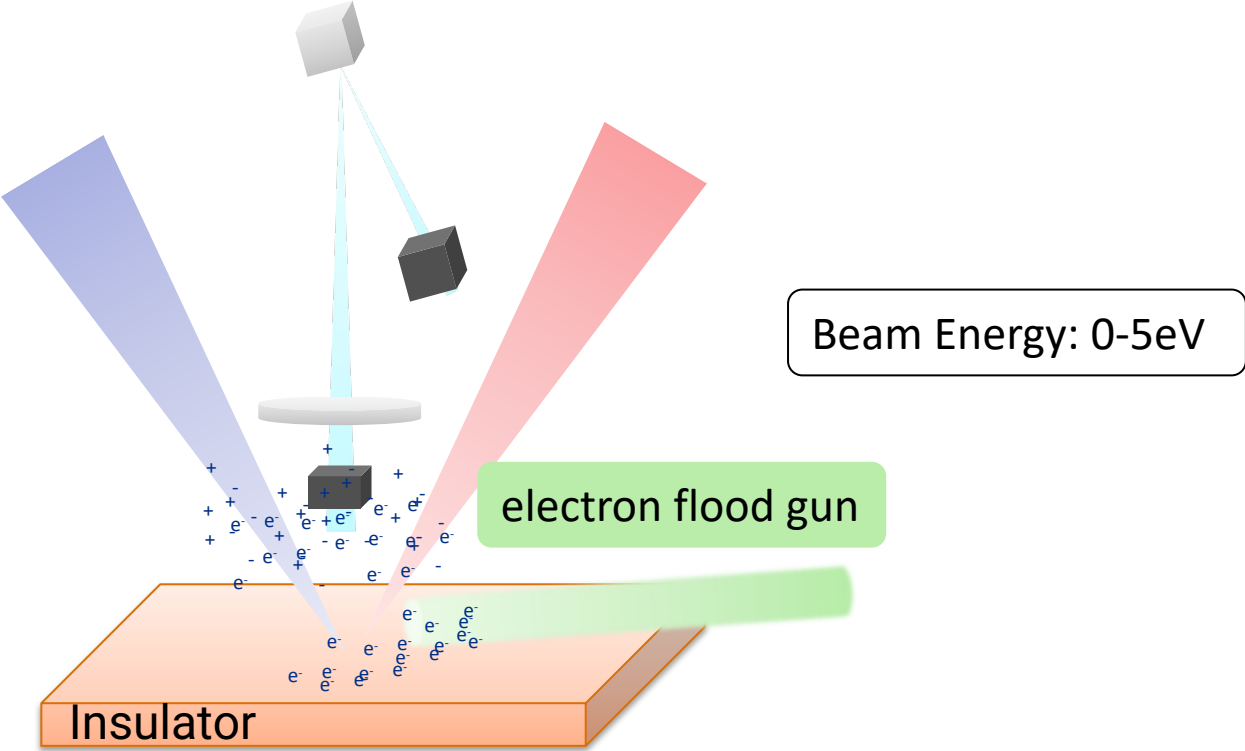
ToF-SIMS: Sputter Gun - Optics



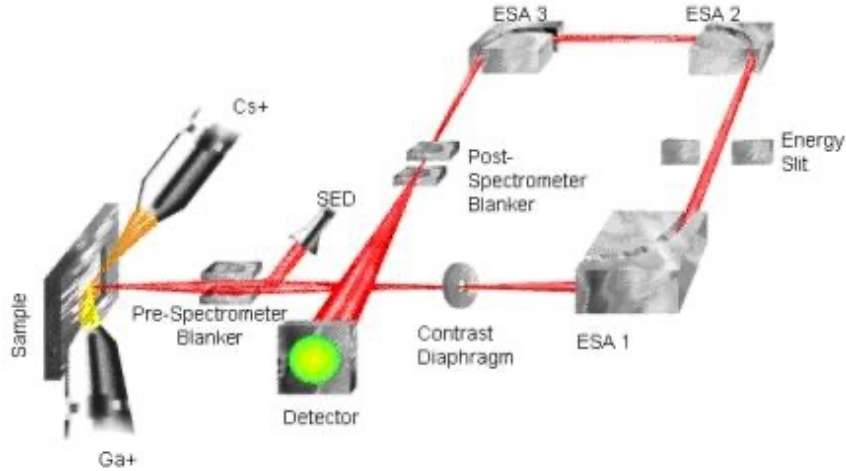
Similar to analysis gun optics

PHI TRIFT III
schematic

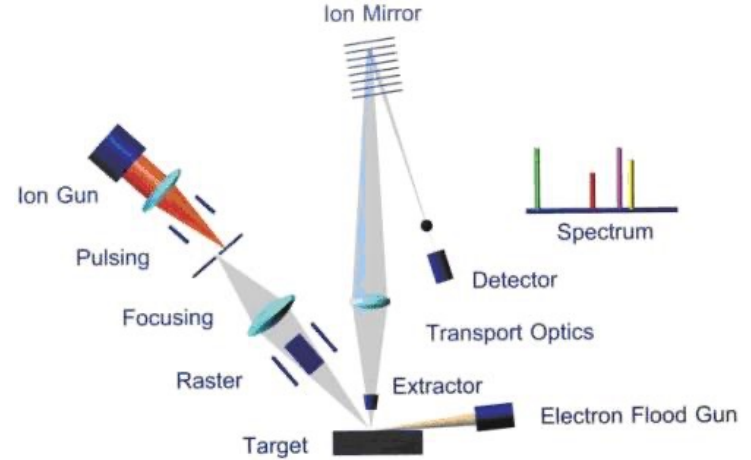
ToF-SIMS: Electron Flood Gun



ToF-SIMS: Mass Spectrometer – Flight Path



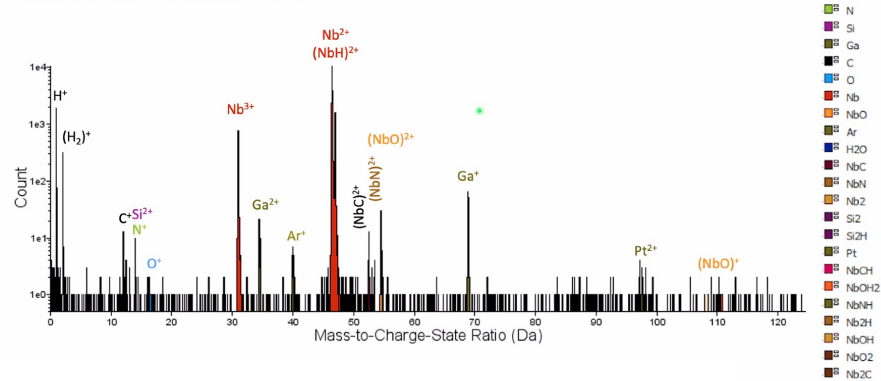
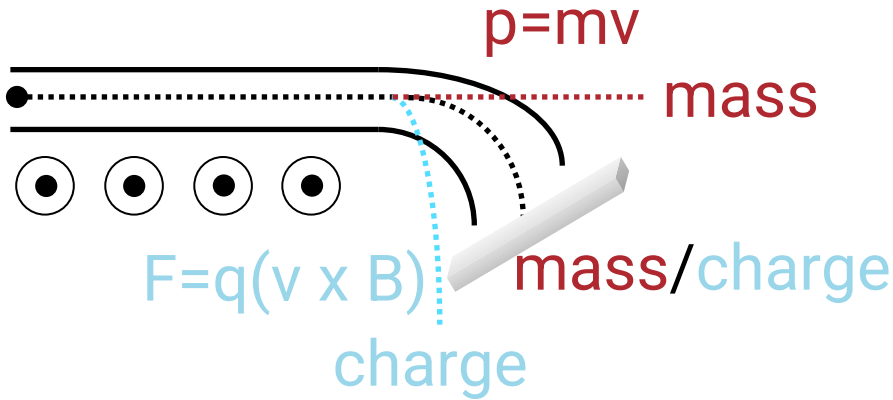
VS.



- Secondary ions directed using an extractor
- 2 main options in terms of flight paths:
 - Circular vs Linear

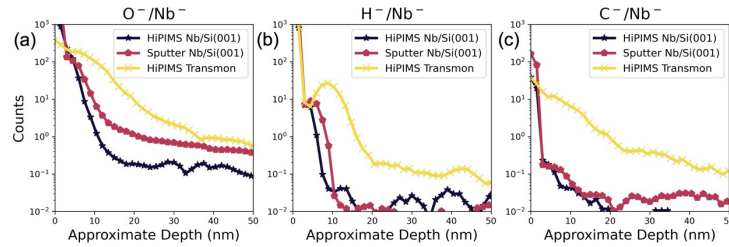
ToF-SIMS: Detector – Mass Spectrometer

Extractor

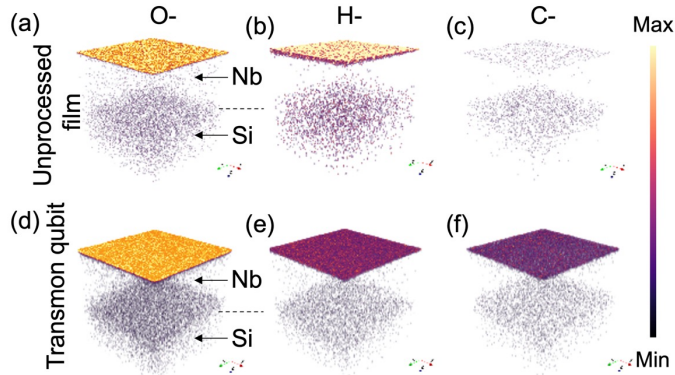


Detector measures m/z ratio

Highlight: Quantifying Impurities in Nb Qubit Films



Depth Profiles of impurities in Nb film

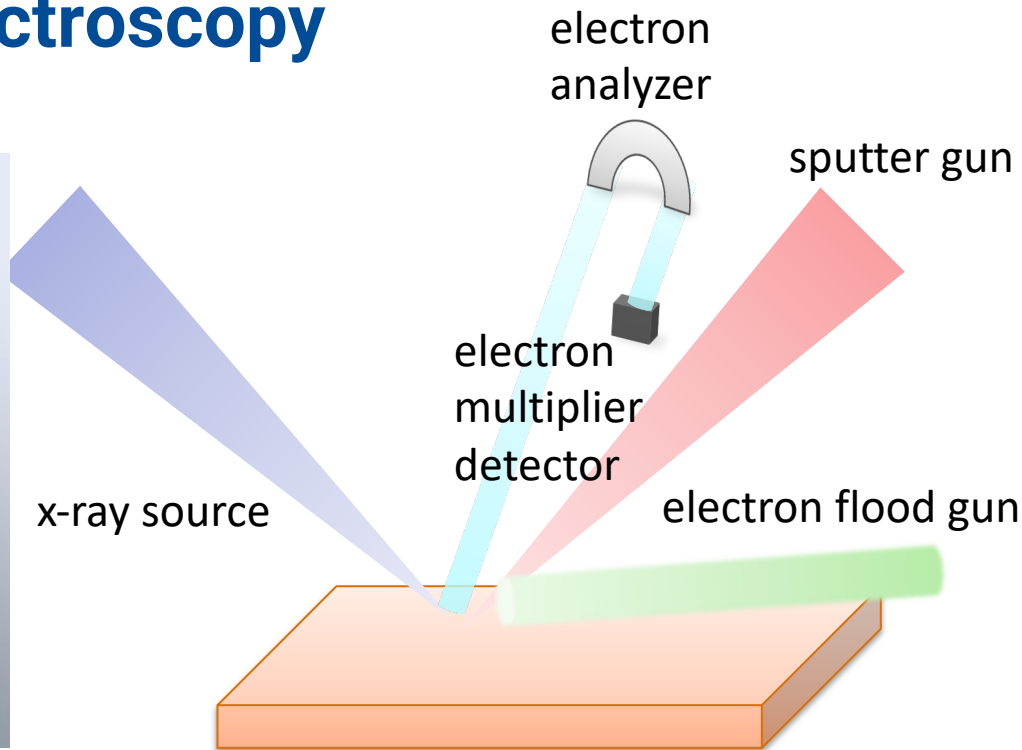


3D representation of impurity concentrations

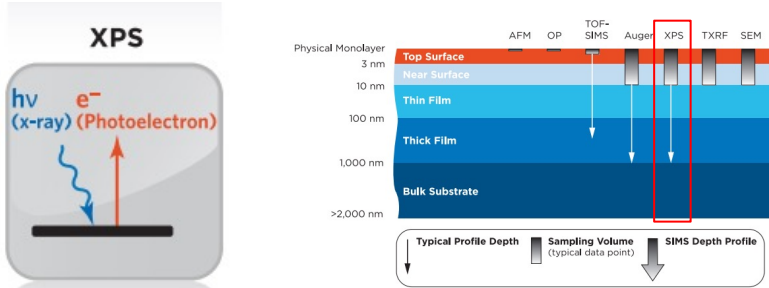
- TOF-SIMS applied for the first time ever to 2D qubits reveal levels of contamination in the Nb pads
- Lithography steps during qubit fabrication lead to incorporation of impurity species including O⁻, H⁻, C⁻, Cl⁻, F⁻, Na⁺, Mg⁺, and Ca⁺
- Evaluating possible effects of the film purity on the microwave dissipation

Appl. Phys. Lett. **120** (4), 044002 (2022)

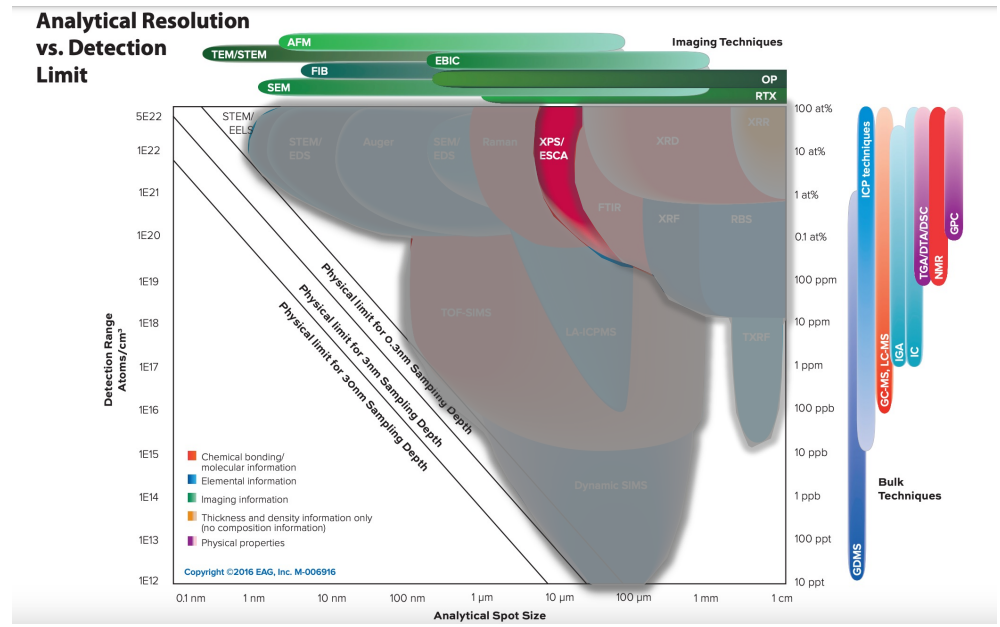
X-Ray Photoelectron Spectroscopy



XPS Basics

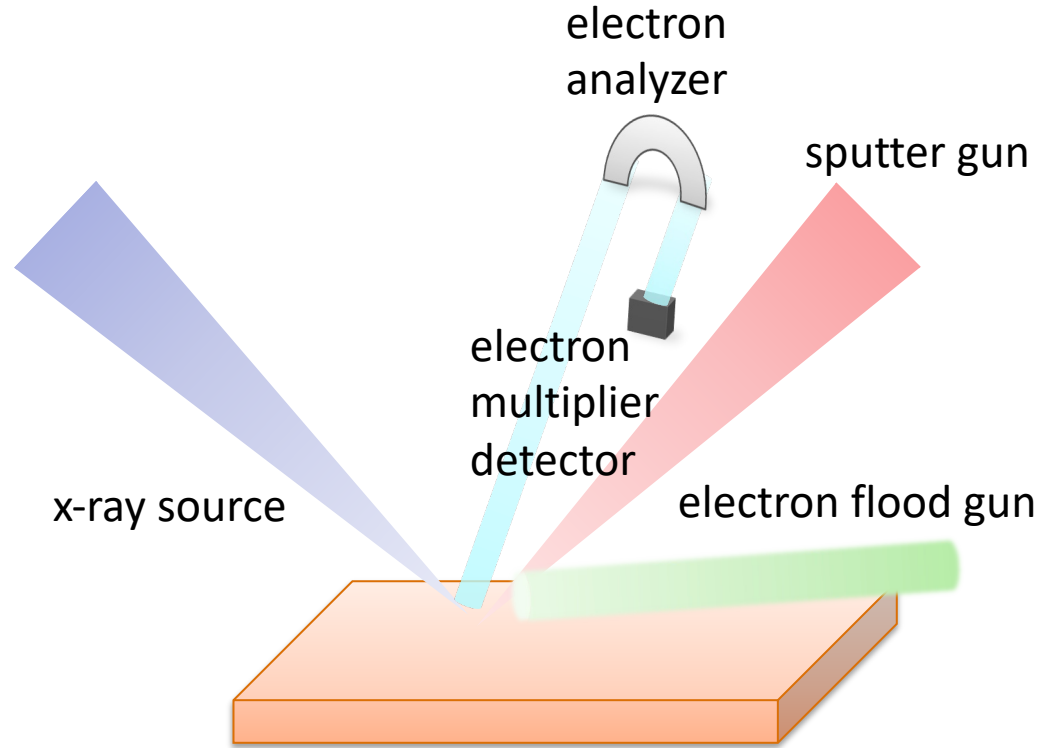


- Sensitive to atom%
- Provides elemental & bonding information
- Detection of low atomic number elements

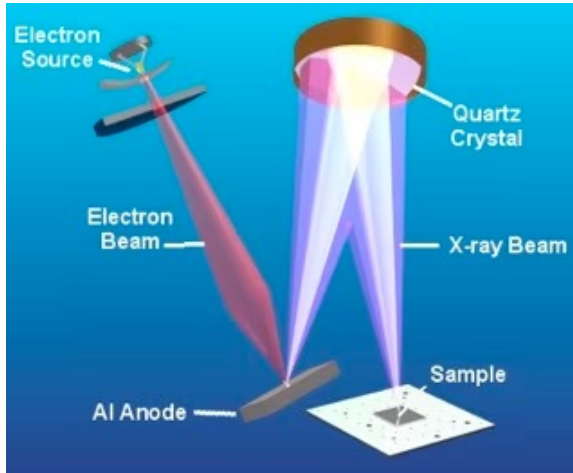


XPS Components

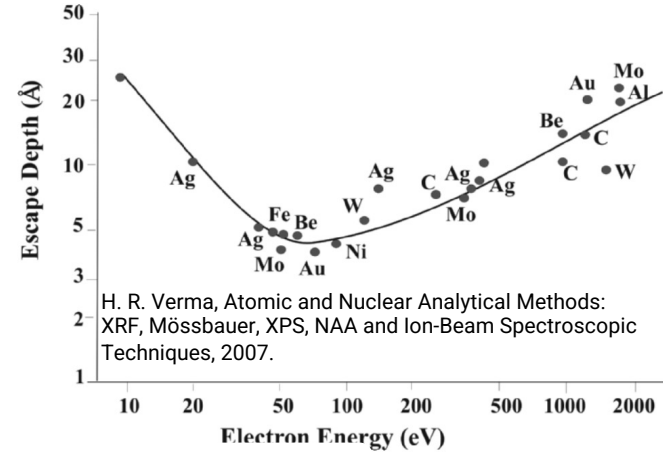
- X-Ray Source
- Sputter gun
- Electron flood gun
- Electron detector



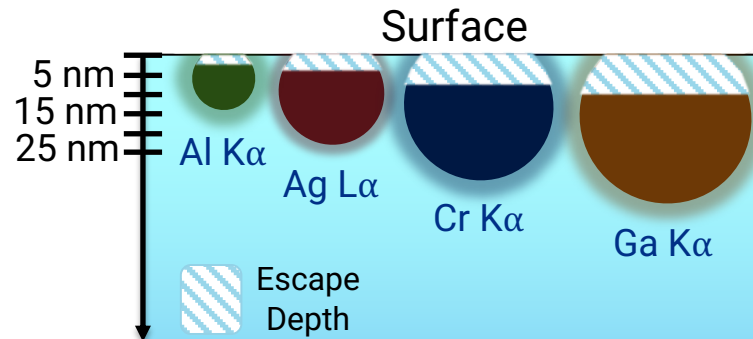
XPS: X-Ray Source



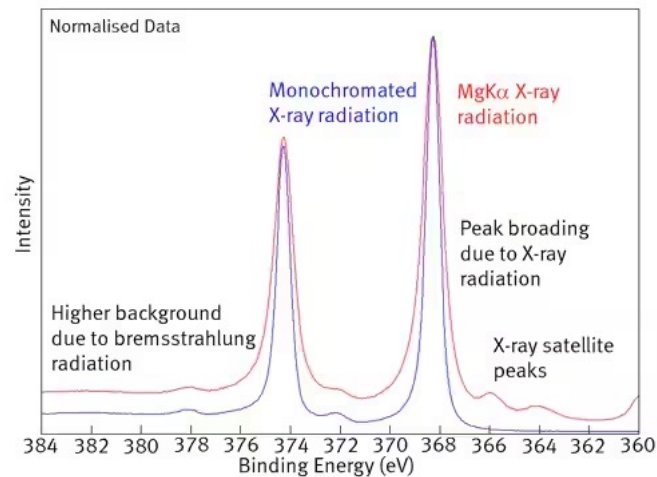
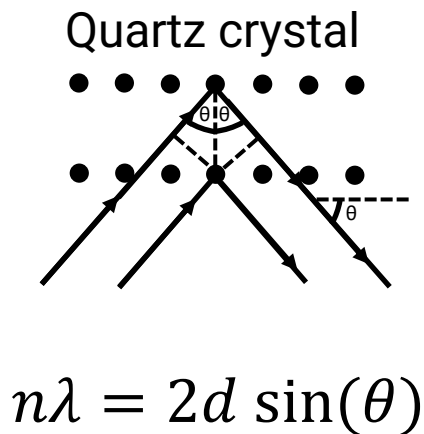
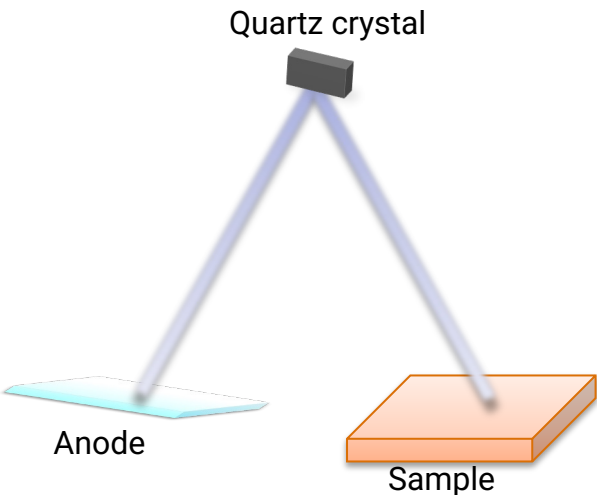
X-Ray Source	Energy (eV)
Al K α	1486.6
Ag L α	2984.3
Cr K α	5414.8
Ga K α	9251.7



- Probe Size: ~500 μm
- Information Depth: ~ 5-15 nm

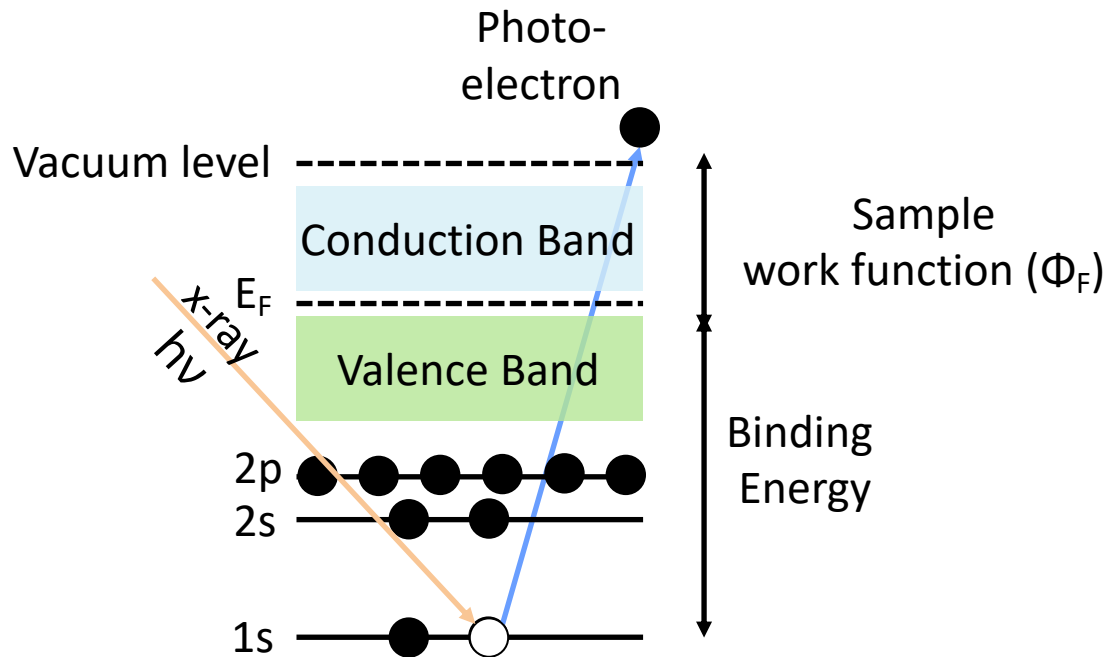


XPS: X-Ray Monochromator



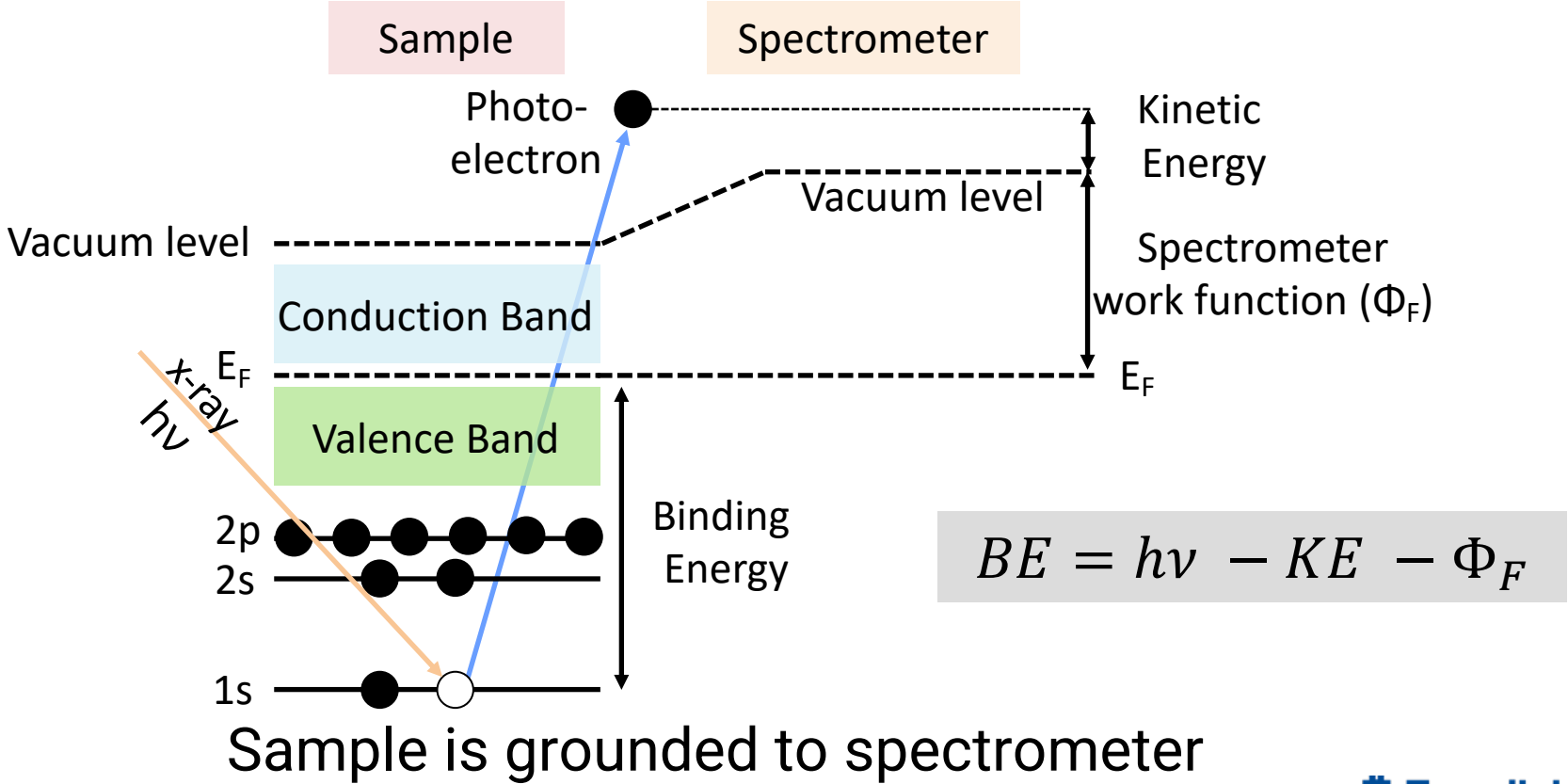
Source: Thermofisher

XPS: Photoelectric Effect

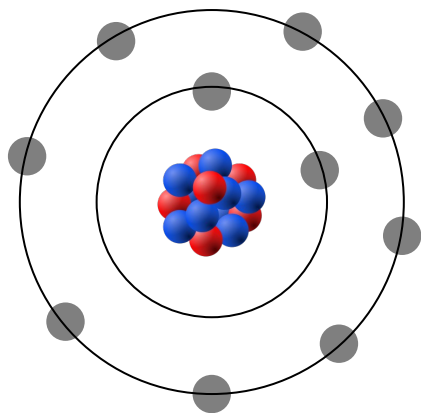


How does BE relate to Φ_F , $h\nu$, and KE of photoelectron?

XPS: Binding Energy

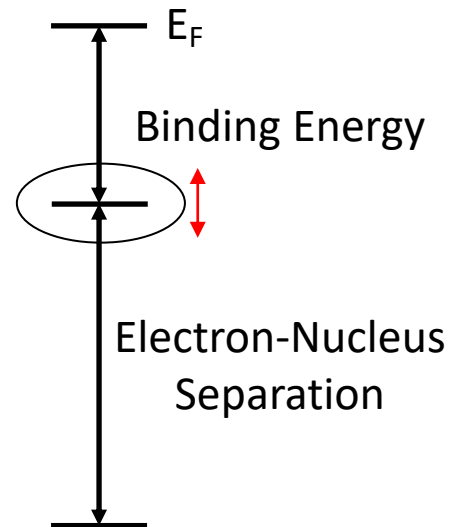


XPS: Local Changes to Binding Energy

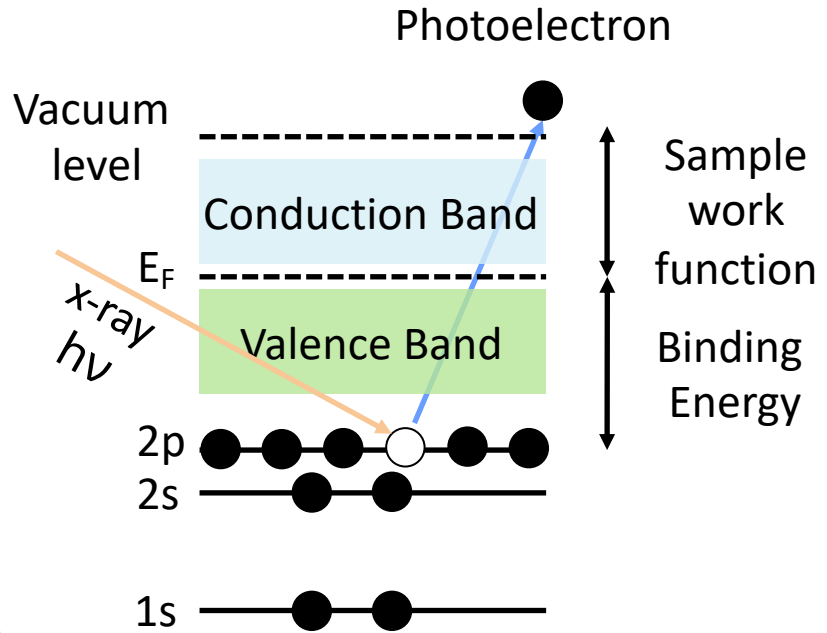
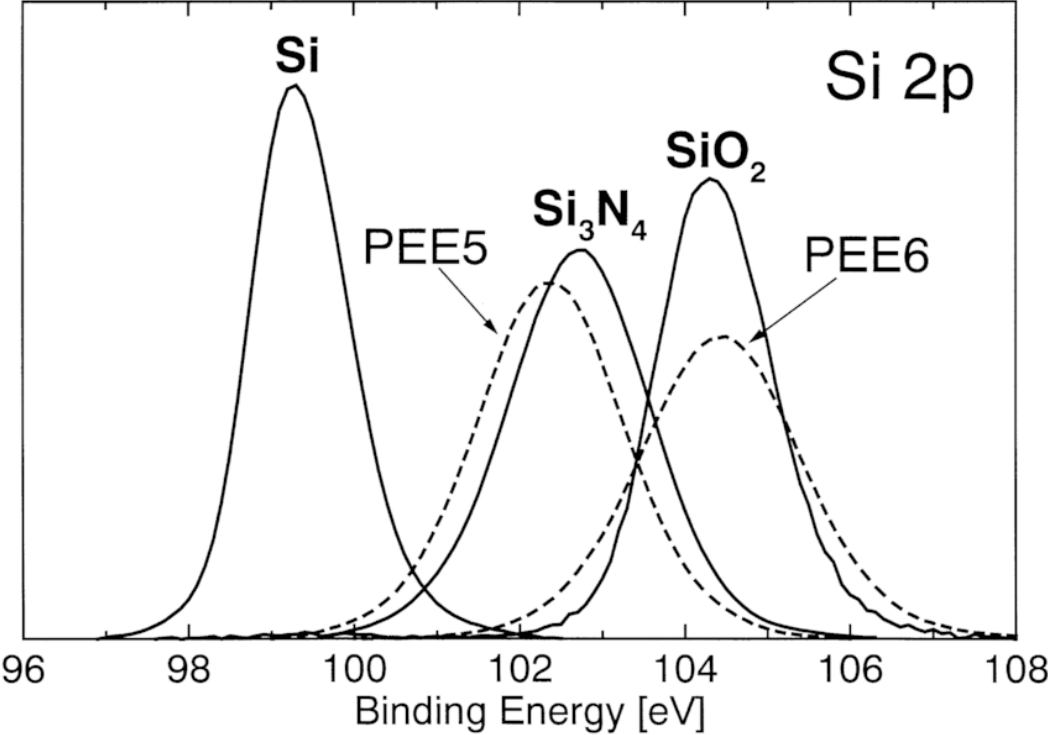


Electron-
electron
repulsion

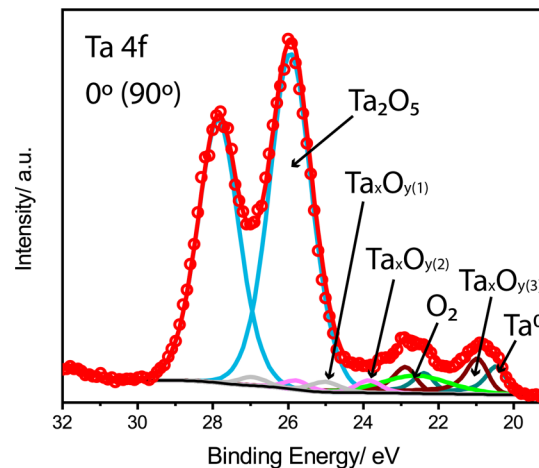
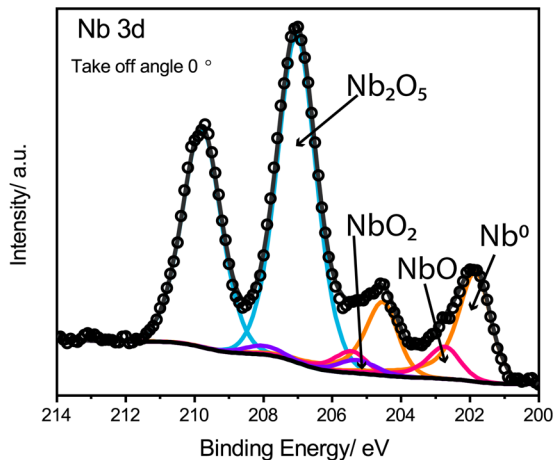
Electron-
nucleus
attraction



XPS: Local Changes to Binding Energy



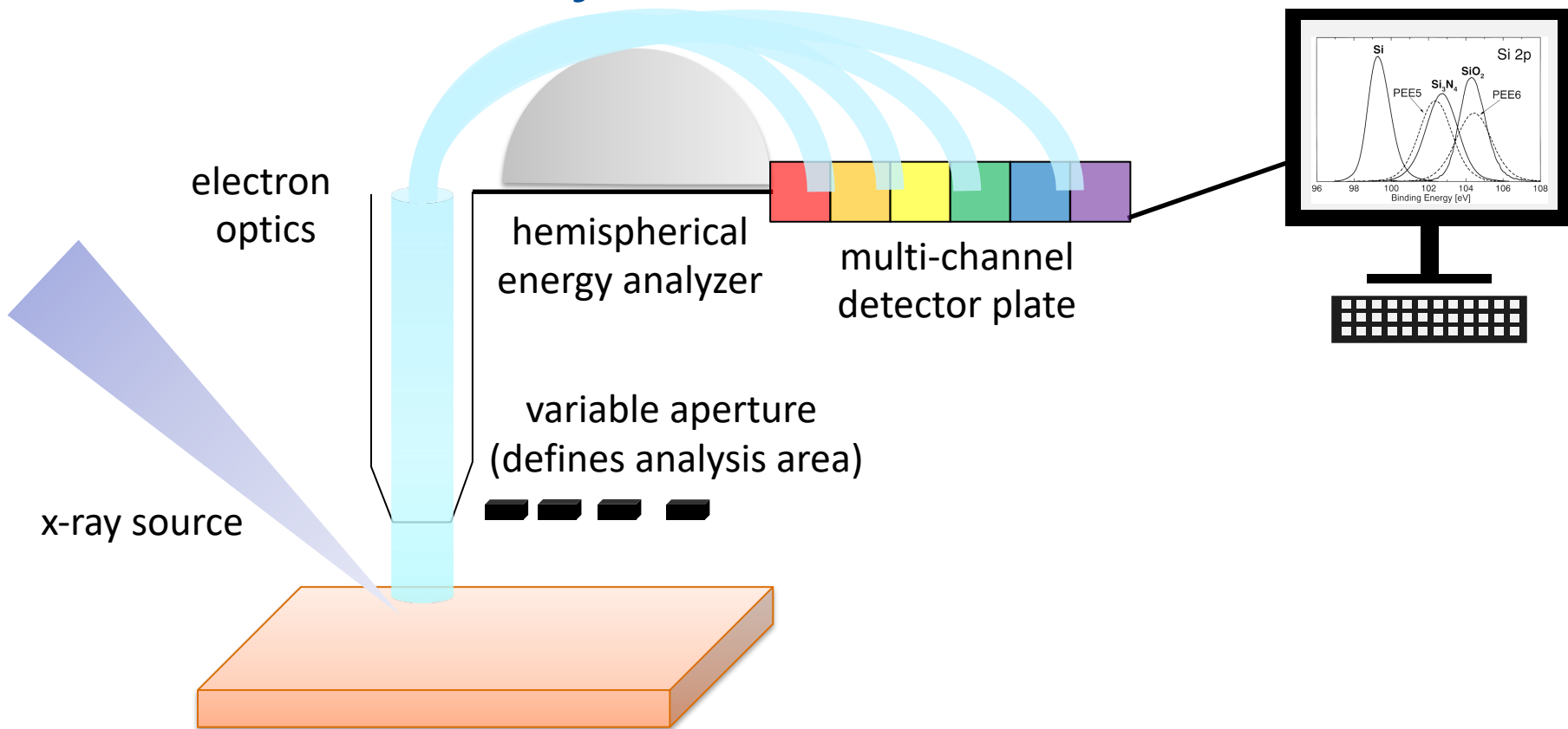
Highlight: Quantifying Impurities in Nb Qubit Films



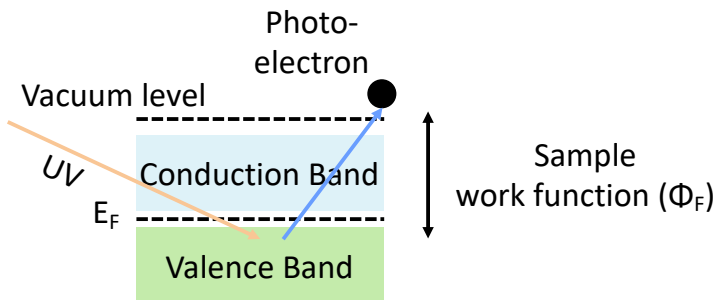
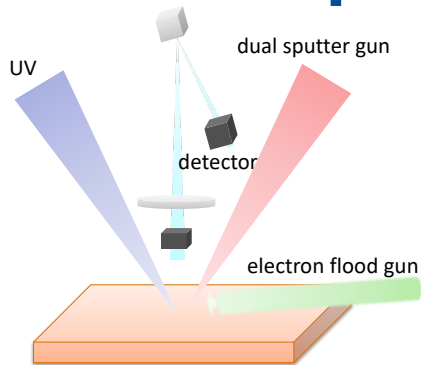
angle		0° (90)		
Species	BE/ eV	$\Delta\text{BE}/ \text{eV}$	FWHM/ eV	Q
Nb^0	201.83	2.7	1.1	22.06
NbO	202.73	2.72	1.1	6.53
NbO_2	205.29	2.7	1.3	2.7
Nb_2O_5	207.03	2.76	1.3	68.7
$\Delta\text{BE}/ \text{eV}_{5-0}$	5.2			

angle		0° (90)		
Species	BE/ eV	$\Delta\text{BE}/ \text{eV}$	FWHM/ eV	Q
Ta^0	20.46	1.92	0.7	4.93
$\text{Ta}_x\text{O}_y(1)$	20.96	1.92	0.7	6.51
$\text{Ta}_x\text{O}_y(2)$	23.86	1.92	0.8	1.66
$\text{Ta}_x\text{O}_y(3)$	25.02	1.92	0.9	0.9
Ta_2O_5	25.94	1.92	1.3	85.99
$\Delta\text{BE}/ \text{eV}_{5-0}$	5.48			

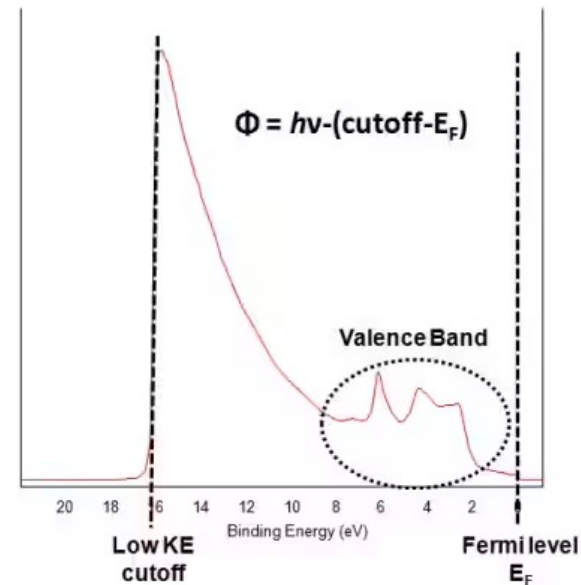
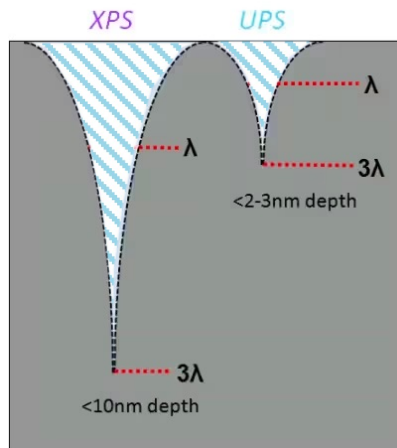
XPS: Electron Analyzer + Detector



Related Topics: UV Photoelectron Spectroscopy



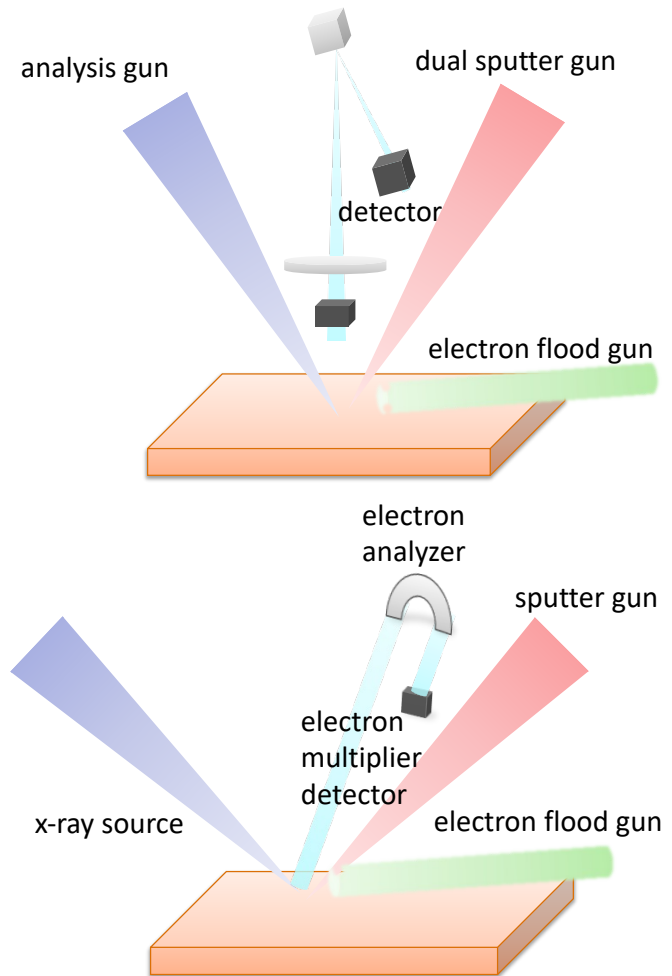
UV Source	Energy (eV)
He I	21.2
He II	40.8



Source: Thermofisher

Summary

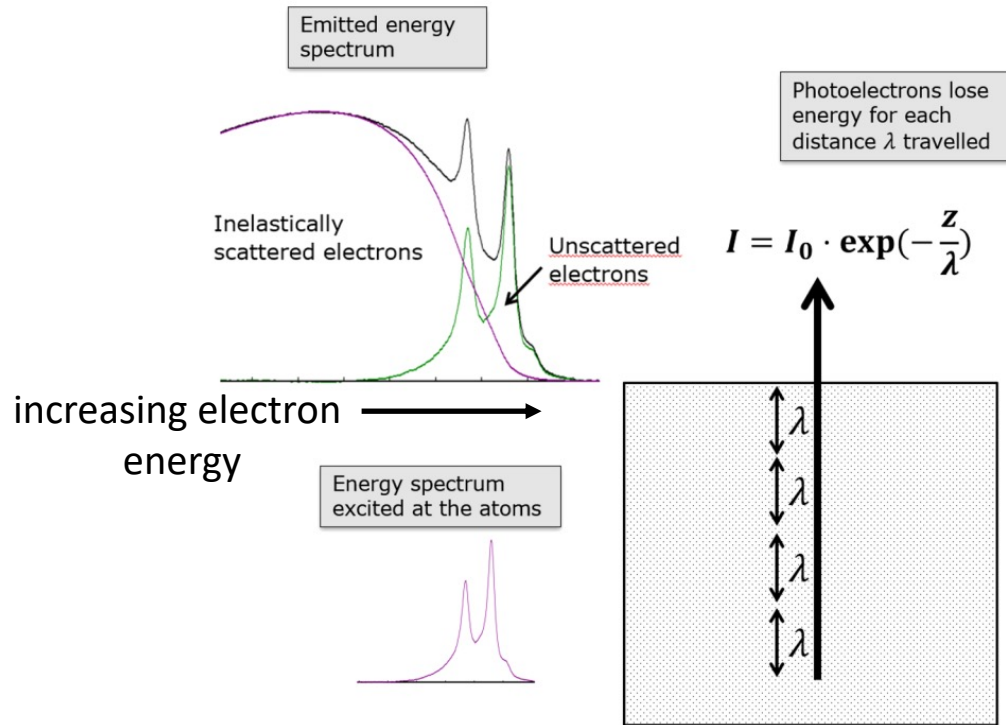
- ToF-SIMS
 - Very sensitive surface analytical technique
 - Allows detection of low Z elements
 - Useful for probing impurities in quantum devices
- XPS
 - Surface analytical technique sensitive to atom%
 - Allows detection of changes in bonding environment
 - Useful for characterizing surface stoichiometry in quantum devices



Appendix

Inelastic Scattering

Origin of variations in XPS peak-background shape



Sven Tougaard; Practical guide to the use of backgrounds in quantitative XPS. Journal of Vacuum Science & Technology A 1 January 2021; 39 (1): 011201. <https://doi.org/10.1116/6.0000661>